MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

SB1045L-MS THRU SB10100L-MS

Product specification





FEATURES

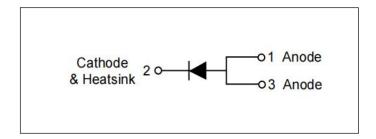
- EXTREMELY LOW VF
- LOW STORED CHARGE, MAJORITY CARRIER CONDUCTION
- LOW POWER LOSS / HIGH EFFICIENCY
- UL 94V0 FLAME RETARDANT EPOXY MOLDING COMPOUND
- HALOGEN FREE

MECHANICAL DATA

- CASE: TRANSFER MOLDED
- LEADS: SOLDERABLE PER MIL-STD-202, METHOD 208
- POLARITY: AS MARKED
- WEIGHT: 0.095 GRAMS (APPROXIMATELY)

Reference News





Marking Information

SB1045L-MS	SB1060L-MS	SB10100L-MS		
SB1045L	SB1060L	SB10100L		



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

FOR CAPACITIVE LOAD, DERATE CURRENT BY 20%

,					
RATINGS		SB1045L-MS	SB1060L-MS	SB10100L-MS	UNITS
MAXIMUM RECURRENT PEAK REVERSE VOLTAGE	V _{RRM}	45	60	100	V
MAXIMUM RMS VOLTAGE	V_{RMS}	31.5	42	70	V
MAXIMUM DC BLOCKING VOLTAGE	V_{DC}	45	60	100	V
MAXIMUM AVERAGE FORWARD RECTIFIED CURRENT SEE FIG.1 PER LEG		10		A	
PEAK FORWARD SURGE CURRENT, 8.3ms SINGLE HALF SINE-WAVE SUPERIMPOSED ON RATED LOAD PER LEG	I_{FSM}	250		A	
STORAGE TEMPERATURE RANGE	T_{STG}	- 65 TO + 175		$^{\circ}\mathbb{C}$	
OPERATING JUNCTION TEMPERATURE RANGE	T_{J}	- 55 TO + 150		$^{\circ}\mathbb{C}$	
ELECTRICAL CHARACTERISTICS	T T				T
CHARACTERISTICS	SYMBOL	SB1045L-MS	SB1060L-MS	SB10100L-MS	UNITS
MAXIMUM FORWARD VOLTAGE AT I_F = 10A T_J =25°C		0.50	0.65	0.75	
T _J =125 ℃		0.43	0.55	0.65	
TYPICAL FORWARD VOLTAGE AT $I_F = 1$ A $T_J = 125$ °C	VF	0.28	0.35	0.42	V
TYPICAL FORWARD VOLTAGE AT I_F = 3A T_J =125°C		0.33	0.38	0.48	
TYPICAL FORWARD VOLTAGE AT $I_F = 5A$ $T_J = 125^{\circ}C$	1 -	0.36	0.42	0.55	
MAXIMUM REVERSE CURRENT AT 25°C PER LEG (NOTE 1)	I_R	0	0.1		
MAXIMUM REVERSE CURRENT AT 125°C PER LEG (NOTE 1)	I_R	20		mA	
THERMAL CHARACTERISTICS (T $_{\mathrm{C}}$ =25 $^{\circ}$ C UNLESS OTHERWI	SE NOTED)				
PARAMETER	SYMBOL	SB1045L-MS	SB1060L-MS	SB10100L-MS	UNITS
TYPICAL THERMAL RESISTANCE JUNCTION TO CASE PEILEG	R _{θjc}	23		°C/W	

NOTES: 1. PULSE TEST: 300µS PULSE WIDTH, 1% DUTY CYCLE.



RATINGS AND CHARACTERISTIC CURVES OF SB1045L-MS THRU SB10100L-MS

FIG. 1-FORWARD CURRENT DERATING CURVE

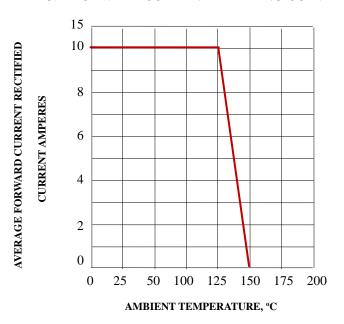


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE RATING

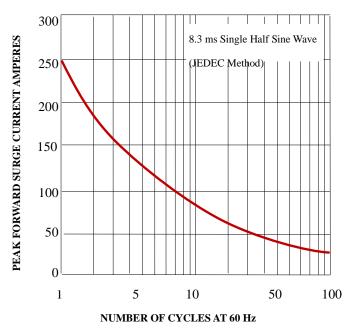
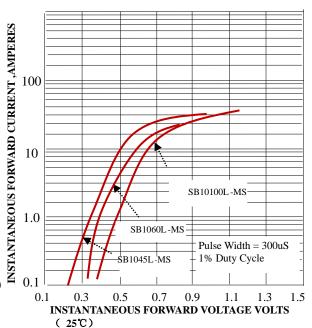


FIG. 3- TYPICAL REVERSE CHARACTERISTICS

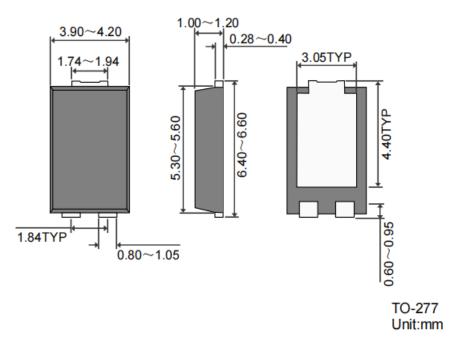
INSTANTANEOUS REVERSE CURRENT, MILLIAMPERES 100 Tj=125°C 10.0 Tj=100°C 1.0 Tj=25°C 0.1 100 0 40 20 60 80 PERCENT OF RATED VOLTAGE PEAK REVERSE VOLTAGE (%)

FIG. 4- TYPICAL INSTANTANEOUS FORWARD CHARCTERISTICS

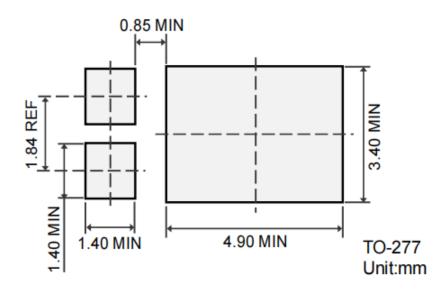




Package Outline Dimensions



Suggested Solder Pad Layout



REEL SPECIFICATION

P/N	PKG	QTY
SB1045L-MS THRU SB10100L-MS	TO-277	5000



Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents—or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.